2SC4906

Silicon NPN Epitaxial

HITACHI

Application

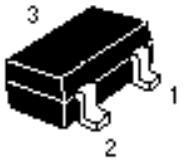
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
  f_T = 5.8 GHz Typ
- High gain, low noise figure
  PG = 12.0 dB Typ, NF = 1.6 dB Typ at f = 900 MHz

Outline

CMPAK



1. Emitter
2. Base
3. Collector

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

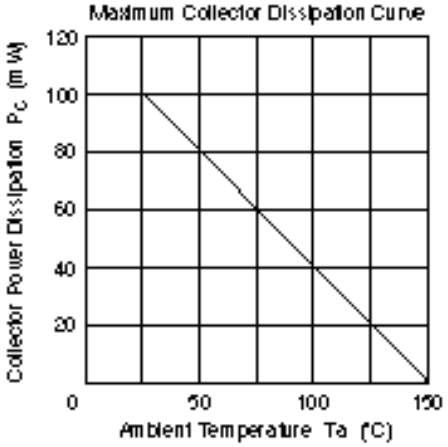
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

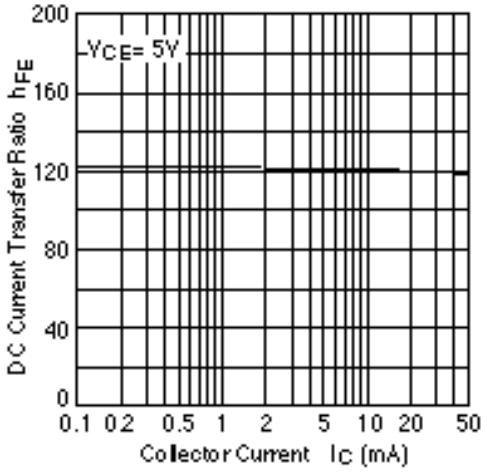
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	I_C = 10 µA, I_E = 0
Collector cutoff current	I_{CBO}	—	—	1	µA	V_{CB} = 15 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 12 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 2 V, I_C = 0
DC current transfer ratio	h_{FE}	50	120	250		V_{CE} = 5 V, I_C = 20 mA
Collector output capacitance	Cob	—	0.9	1.4	pF	V_{CB} = 5 V, I_E = 0, f = 1 MHz
Gain bandwidth product	f_T	4	5.8	—	GHz	V_{CE} = 5 V, I_C = 20 mA
Power gain	PG	9.5	12.0	—	dB	V_{CE} = 5 V, I_C = 20 mA, f = 900 MHz
Noise figure	NF	—	1.6	3.0	dB	V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz

Note: Marking is “YN–”.

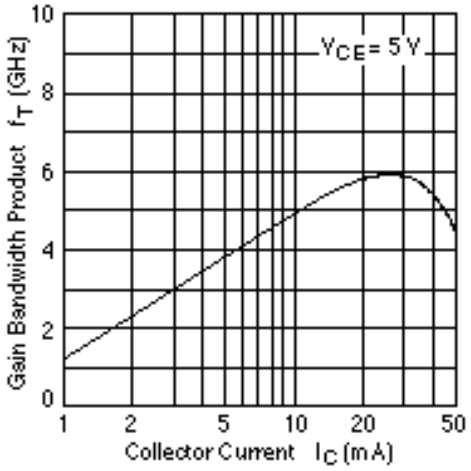
Maximum Collector Dissipation Curve



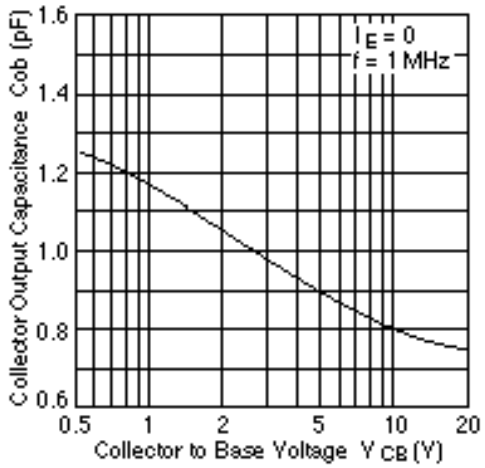
DC Current Transfer Ratio vs. Collector Current



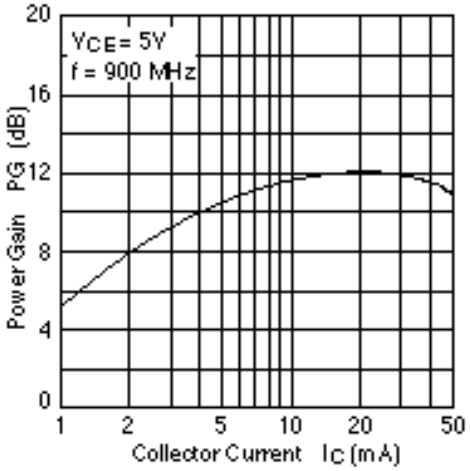
Gain Bandwidth Product vs. Collector Current



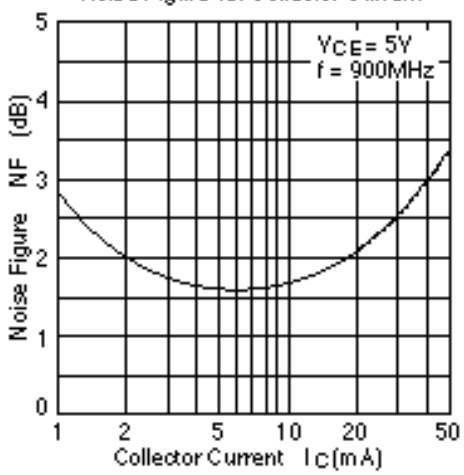
Collector Output Capacitance vs. Collector to Base Voltage



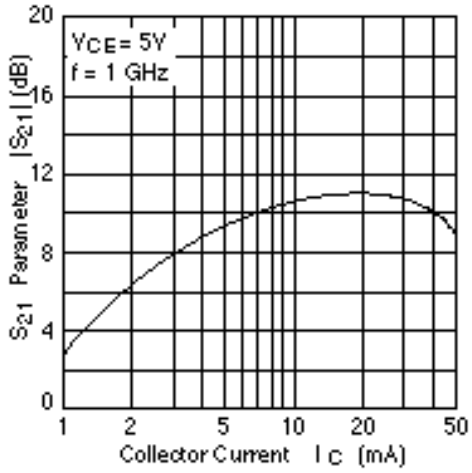
Power Gain vs. Collector Current



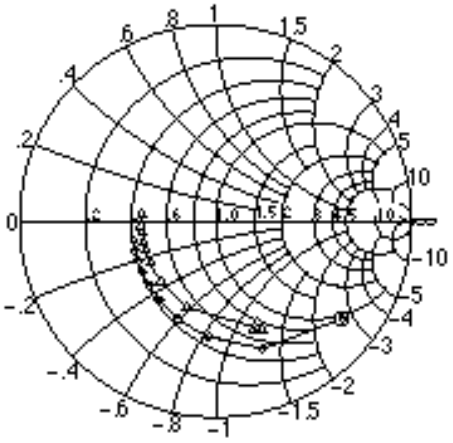
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current

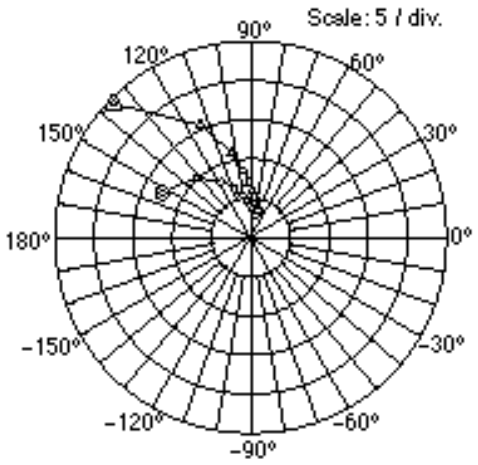


S11 Parameter vs. Frequency



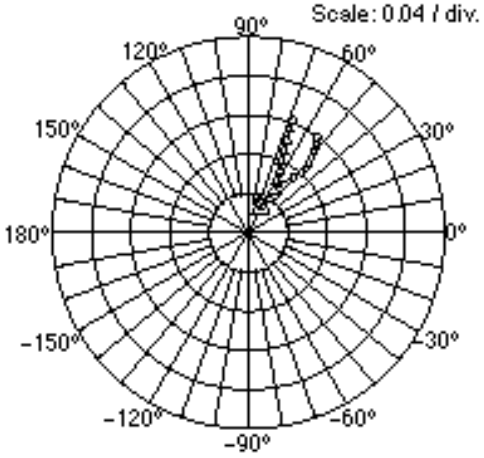
Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(IC = 5 mA)
(IC = 20 mA)

S21 Parameter vs. Frequency



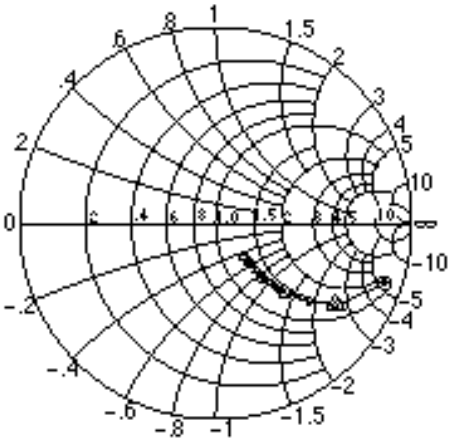
Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S12 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 MHz (100 MHz step)
(I_C = 5 mA)
(I_C = 20 mA)

S Parameter (V_{CE} = 5 V, I_C = 5 mA, Z_O = 50 Ω, Emitter common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.813	–37.6	12.67	153.5	0.0354	71.0	0.912	–19.4
200	0.693	–69.6	10.22	132.5	0.0587	57.7	0.756	–32.9
300	0.591	–93.5	8.04	118.3	0.0727	51.0	0.623	–39.9
400	0.534	–111.3	6.54	108.7	0.0812	48.7	0.536	–43.6
500	0.492	–124.9	5.44	101.4	0.0880	48.2	0.477	–45.6
600	0.471	–135.5	4.66	95.8	0.0943	48.8	0.437	–46.6
700	0.453	–144.9	4.07	91.0	0.100	49.9	0.408	–47.5
800	0.445	–153.1	3.61	86.5	0.107	51.2	0.388	–48.7
900	0.438	–160.1	3.25	82.6	0.114	52.9	0.373	–49.7
1000	0.429	–166.4	2.96	79.2	0.120	54.3	0.362	–50.9

S Parameter (V_{CE} = 5 V, I_C = 20 mA, Z_O = 50 Ω, Emitter common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.583	–68.6	24.42	135.9	0.0274	63.1	0.741	–34.5
200	0.463	–108.7	15.65	114.4	0.0399	57.0	0.502	–46.7
300	0.416	–132.2	10.99	103.4	0.0500	59.1	0.382	–49.6
400	0.396	–147.6	8.46	96.8	0.0596	61.8	0.320	–49.8
500	0.388	–156.9	6.85	91.9	0.0699	63.3	0.285	–49.3
600	0.385	–163.6	5.77	87.9	0.0798	65.3	0.263	–48.9
700	0.379	–170.3	4.97	84.5	0.0908	66.6	0.249	–49.1
800	0.383	–175.8	4.37	81.2	0.102	67.4	0.238	–49.2
900	0.389	179.2	3.92	78.1	0.113	68.1	0.231	–49.8
1000	0.380	174.7	3.55	75.6	0.123	68.4	0.226	–51.2

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